

## Silicon PNP transistor epitaxial type A5916

### [ Applications ]

DC-DC convertor  
Strobe flash

### [ Feature ]

High DC gain  $hFE= 120-390$  at  $VCE= -2V, IC= -0.1A$   
 Low collector saturation voltage  $VCE(sat)= -0.5V$  (Max.) at  $IC= -2A, IB= -0.1A$

### [ Absolute maximum ratings (Ta=25C) ]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-30	V
Collector-emitter voltage	VCEO	-30	V
Emitter-base voltage	VEBO	-6	V
Collector current (DC)	IC	-3	A
Collector current (Pulse)	ICP	-5	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

### [ Electrical characteristics (Ta=25C) ]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-30	-	-	V	IC= -50uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	-30	-	-	V	IC= -1mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	-6	-	-	V	IE= -50uA, IC= 0A
Collector cut-off current	ICBO	-	-	-100	nA	VCB= -20V, IE= 0A
Emitter cut-off current	IEBO	-	-	-100	nA	VEB= -5V, IC= 0A
DC current gain	hFE	120	-	390	-	VCE= -2V, IC= -0.1A
Collector-emitter saturation voltage	VCE(sat)	-	-	-0.5	V	IC= -2A, IB= -0.1A
Transition frequency	fT	-	190	-	MHz	VCE= -10V, IE= 0.5A
Collector output capacitance	Cob	-	35	-	pF	VCB= -10V, f = 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

No. A5916-20070807

Fig.1 IC - VBE(on)  
at VCE = -2V, Ta = 25C

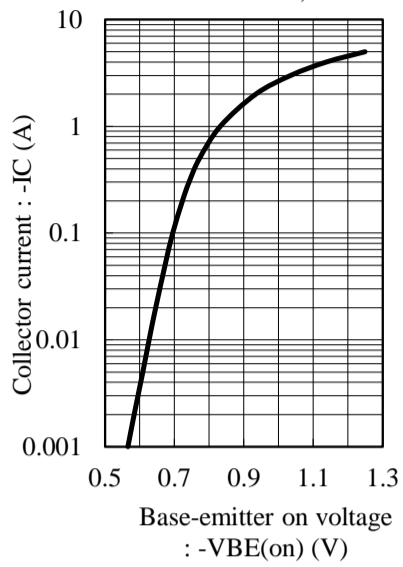


Fig.2 hFE - IC  
at VCE = -2V, Ta = 25C

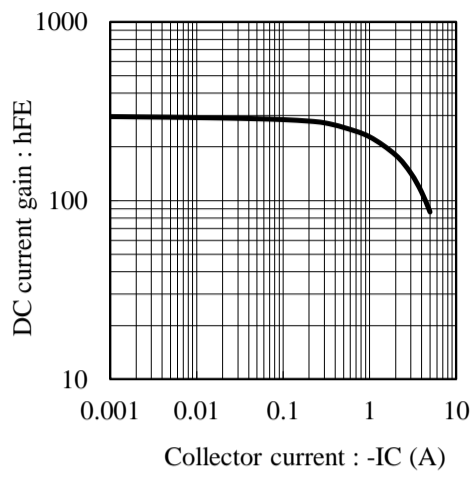


Fig.3 VCE(sat) - IC  
at IC/IB = 20, Ta = 25C

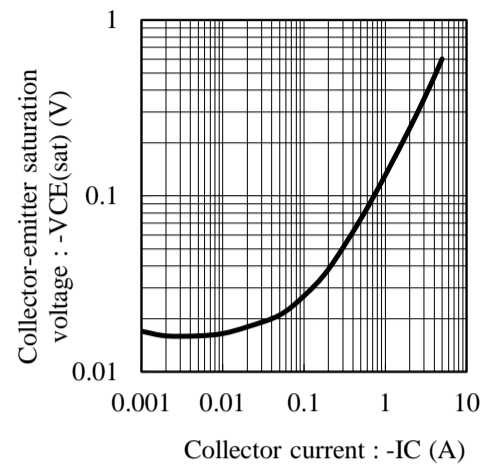


Fig.4 VBE(sat) - IC  
at IC/IB = 20, Ta = 25C

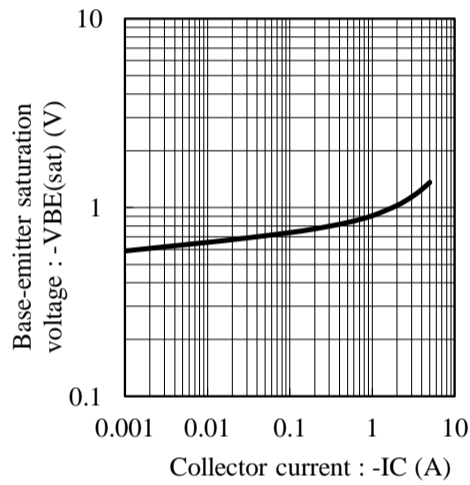


Fig.5 fT - IE  
at VCE = -2V, Ta = 25C

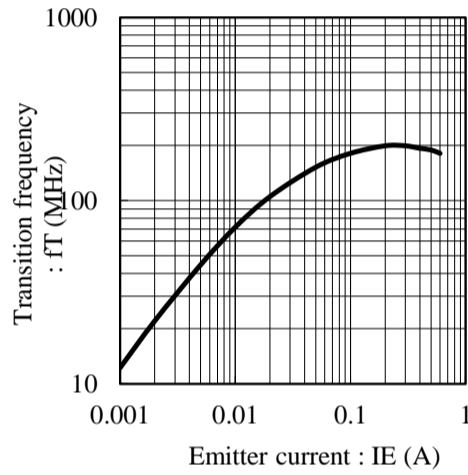


Fig.6 Cob - VCB  
at f = 1MHz, Ta = 25C

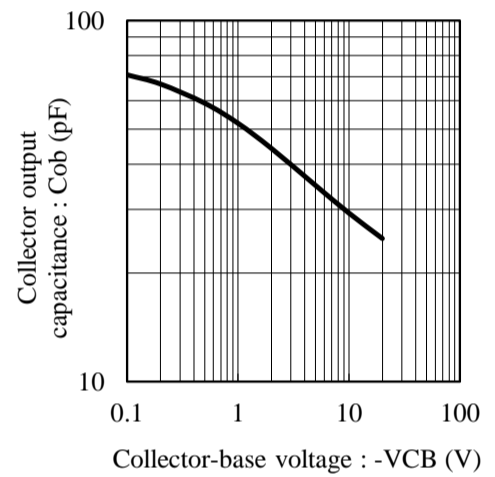


Fig.7 Cib - VEB  
at f = 1MHz, Ta = 25C

